

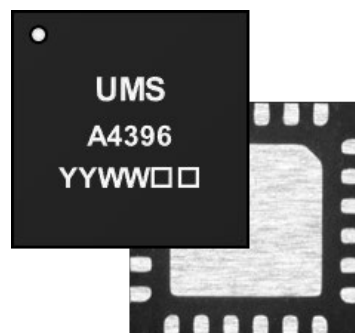
24-30GHz Medium Power Amplifier GaAs Monolithic Microwave IC

Description

The CHA4396-QDG is a three-stage GaAs Medium Power Amplifier operating between 24GHz and 30GHz. This amplifier provides 22dBm maximum Output Power with 17% of Power Added Efficiency and 21dBm Output Power at 1dB gain compression. The circuit exhibits a typical small signal gain of 22dB and 31dBm of Output Third-Order Intercept Point.

This Medium Power Amplifier is dedicated to telecommunication applications and well suited for a wide range of microwave applications and systems including SatCom, RADAR, Radiolink and Space.

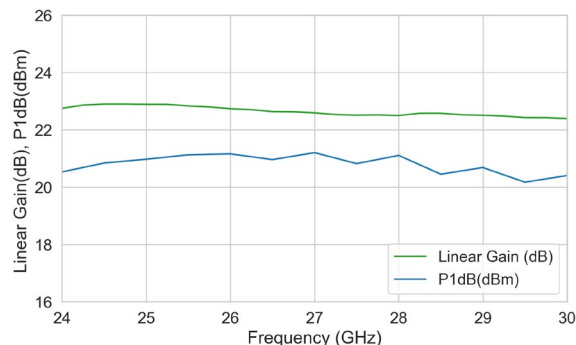
It is available in QFN plastic package. Input and output are 50Ω matched and integrate ESD RF protections.



Main Features

- Frequency range: 24-30GHz
- P1dB = 21dBm
- Linear Gain = 22dB
- ACPR < -35dBc @Pout = 17dBm⁽¹⁾
- EVM < 3.5% @Pout = 17dBm⁽¹⁾
- DC bias: Vd=4V@Id=230mA
- 24L-QFN 4x4mm²
- MSL1

⁽¹⁾ 150MHz Modulation Bandwidth, 16QAM



Main Electrical Characteristics

Tcase = +25°C

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	24		30	GHz
Gain	Linear Gain		22		dB
PAE	Power Added Efficiency		15		%
P1dB	Output Power @1dB comp.		21		dBm

Electrical Characteristics ⁽¹⁾

$T_{case} = +25^{\circ}\text{C}$, $V_d = +4\text{V}$, (T_{case} : QFN backside temperature)

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	24		30	GHz
Gain	Linear gain		22		dB
S_{11}	Input return loss		-12		dB
S_{22}	Output return loss		-12		dB
P1dB	Output power @1dB gain compression		21		dBm
OIP3	Output Third-Order Intercept Point		31		dBm
ACPR	ACPR @Pout = 17dBm with 16QAM modulation (BW = 150MHz, Roll-off = 0.22)		-35		dBc
PAE	Power Added Efficiency @Pin = 3dBm		15		%
NF	Noise Figure		3		
Idq	Quiescent Current		230		mA

⁽¹⁾ Electrical performances are not guaranteed over all recommended operating conditions

Absolute Maximum Ratings ⁽²⁾

$T_{case} = +25^{\circ}\text{C}$

Symbol	Parameter	Value	Unit
Vd	Drain bias voltage	4.5	V
Idq	Maximum quiescent drain bias current	280	mA
Vg	Gate bias voltage	-1.5 to +0.4	V
Pin	Maximum input power	+4	dBm
Tj	Junction temperature ⁽²⁾	<175	°C

⁽²⁾ Operation of this device above anyone of these parameters may cause permanent damage.

Recommended Operating Range ⁽³⁾

Symbol	Parameter	Value	Unit
Vd	Drain bias voltage	3 to 4	V
Idq	Quiescent drain bias current	170 to 230	mA
Vg	Gate bias voltage	-1.5 to -0.4	V
Pin	Maximum input power ⁽³⁾	+3	dBm
Tcase	Operating temperature range	-40 to +85	°C
Tstg	Storage temperature range	-55 to +150	°C

⁽³⁾ Electrical performances are defined for specified test conditions

Typical Bias Conditions $T_{case} = +25^{\circ}\text{C}$

Symbol	Parameter	Value	Unit
VG1, VG2, VG3	Gate voltage tuned for $I_{dq} = 230\text{mA}$	-0.3	V
VD1, VD2, VD3	Drain voltage	4	V

“Power ON” sequence

1. Ground the device
2. Set the gate voltage to -1.5V
3. Apply the drain voltage V_d (typically +4V)
4. Increase V_g up to quiescent bias drain current I_{dq}
5. Apply RF signal

“Power OFF” sequence

1. Turn off RF signal
2. Decrease the gate voltage to -1.5V
3. Decrease the drain voltage to 0V
4. Turn off V_d supply
5. Turn off V_g supply

Device thermal performances

All the figures given in this section are obtained assuming that the QFN device is only cooled down by conduction through the package thermal pad (no convection mode considered).

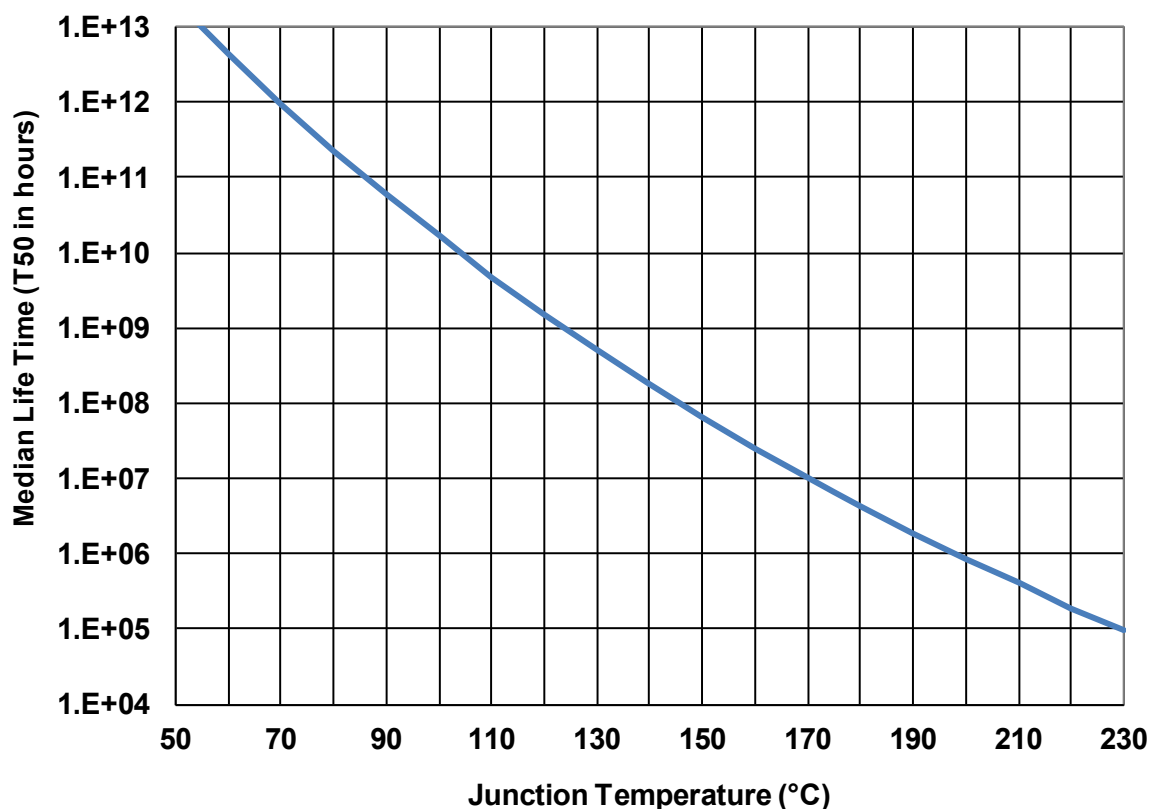
The temperature is monitored at the package backside interface (Tcase).

For nominal operating, the system maximum temperature must be adjusted in order to guarantee that Tjunction remains below the maximum value specified in the Absolute Maximum Ratings table. So the system PCB must be designed to comply with this requirement

Parameter	Biasing conditions	T _{JUNCTION} (°C)	R _{TH} (°C/W)	T50 (hours)
R _{TH} ⁽¹⁾ Thermal Resistance (Junction to QFN Backside)	Vd=4V Pout=22dBm Pdis=0.85W	165	95	2E+7
	Vd=4V Small Signal Pdis=0.9W	170	95	1E+7

⁽¹⁾ Assuming 85°C Tcase

Median Life Time versus Junction Temperature

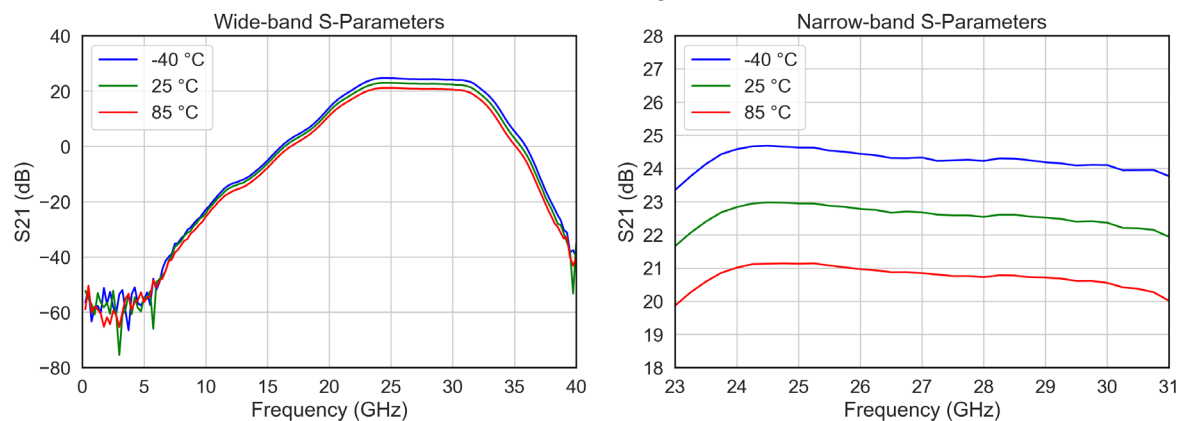


Typical S-Parameters Board Measurements

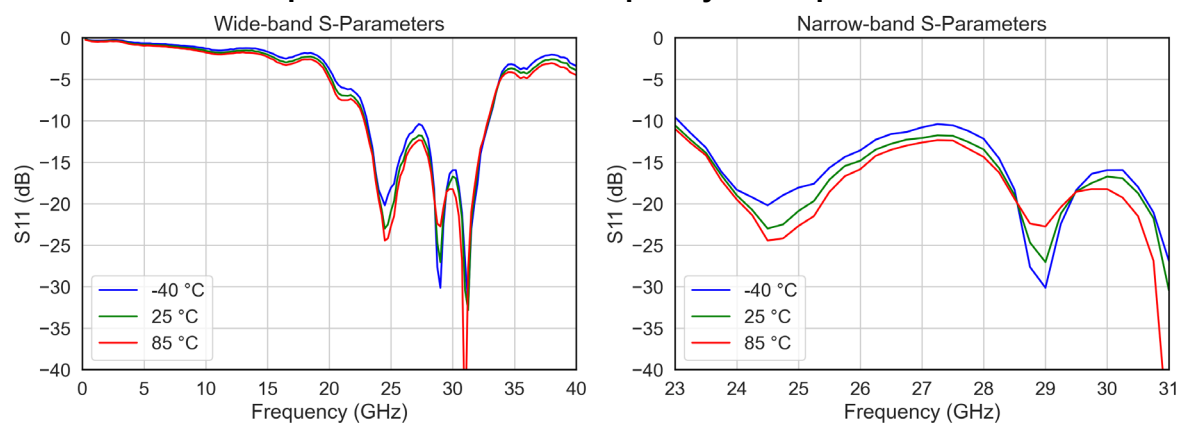
Test conditions : CW, $V_d = +4V$, $I_d = 230mA$, $T_{case} = -40^{\circ}C/25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes

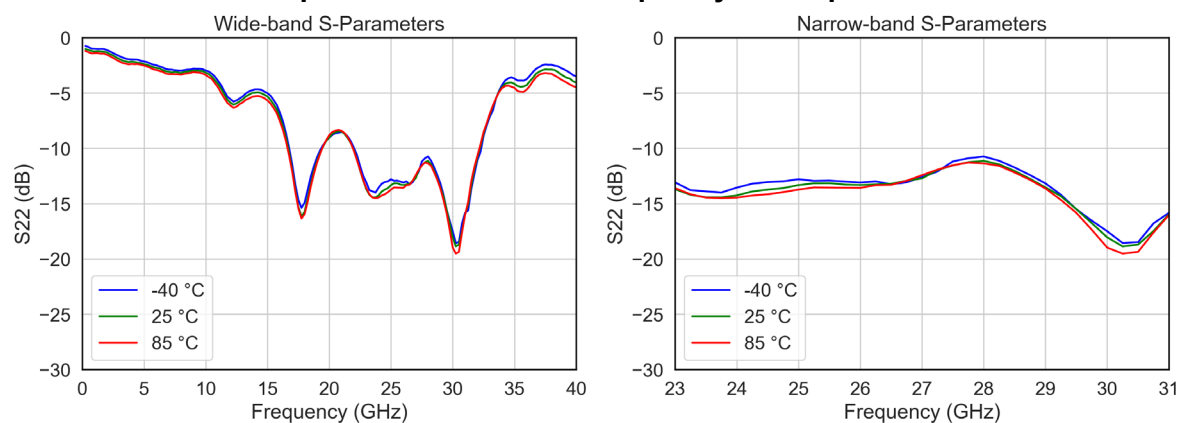
Linear Gain vs. Frequency & Temperature



Input Return Loss vs. Frequency & Temperature

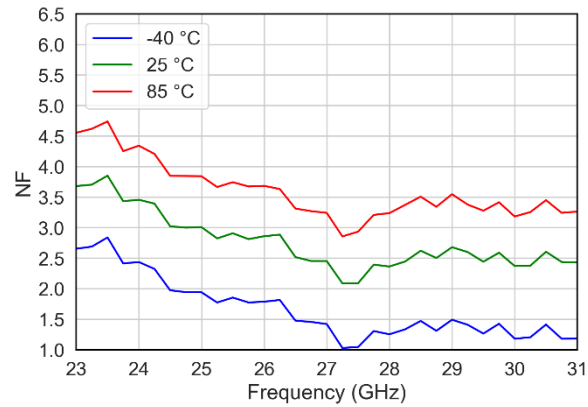


Output Return Loss vs. Frequency & Temperature



Typical Board Measurements : Noise Figure

Test conditions : CW, $V_d = +4V$, $I_d = 230mA$, $T_{case} = -40^{\circ}C/25^{\circ}C/85^{\circ}C$

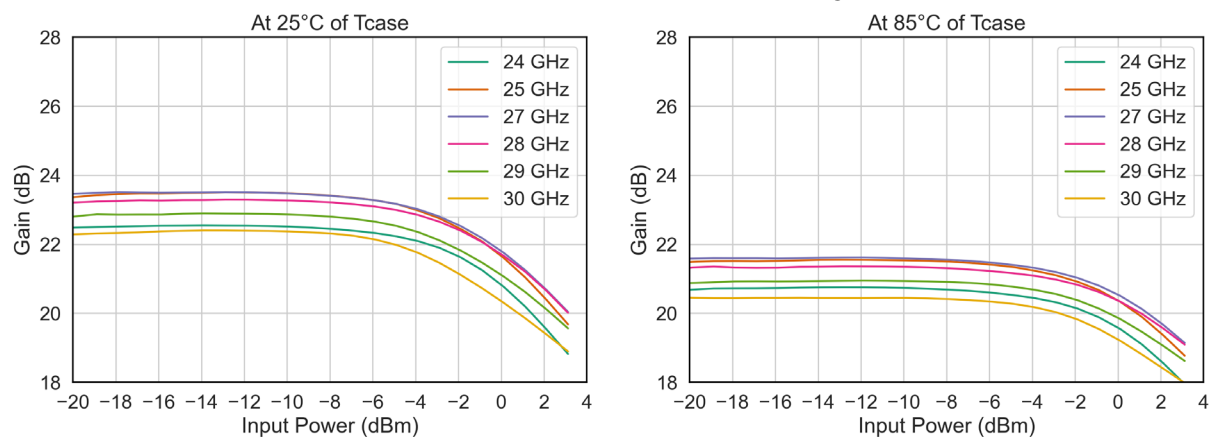
Noise Figure vs. Frequency & Temperature

Typical CW Board Measurements vs. Input Power

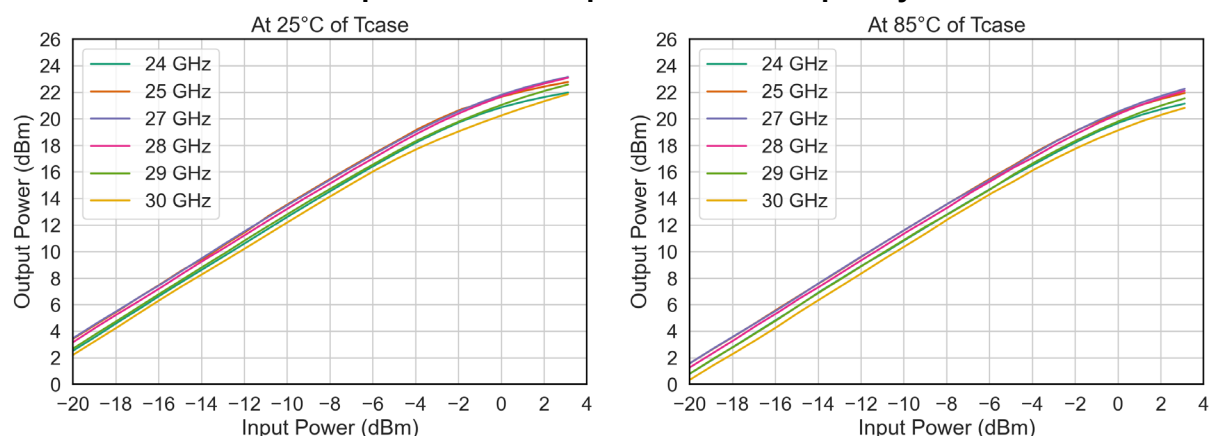
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = +25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes

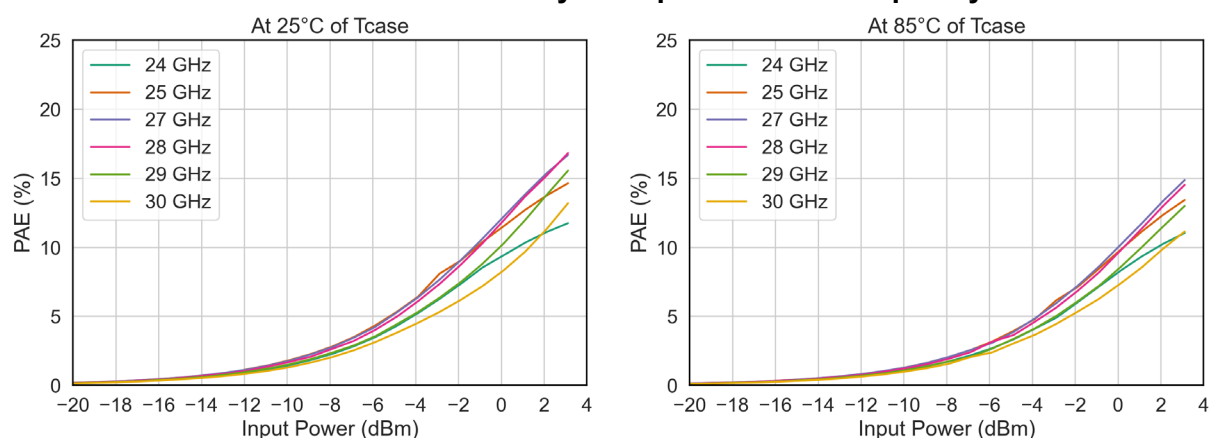
Gain vs. Input Power & Frequency



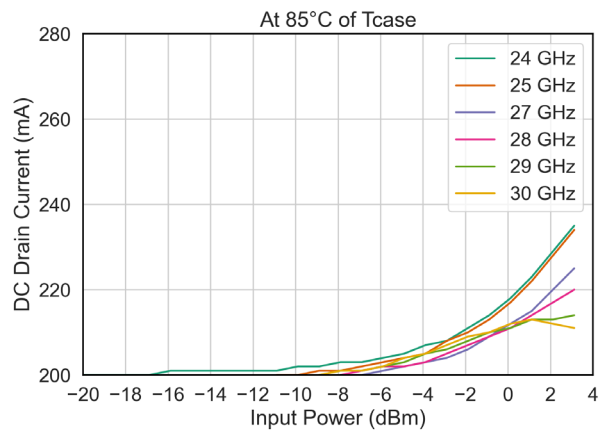
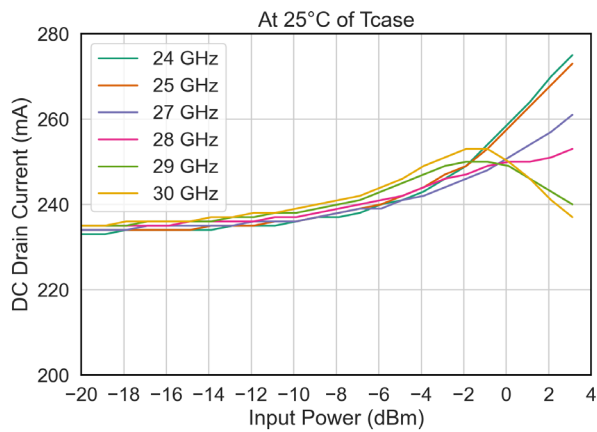
Output Power vs. Input Power & Frequency



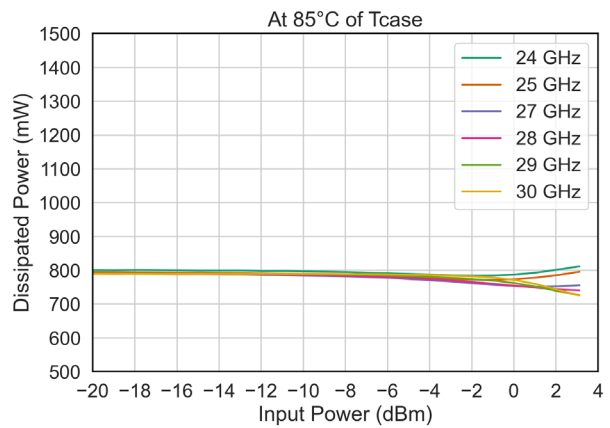
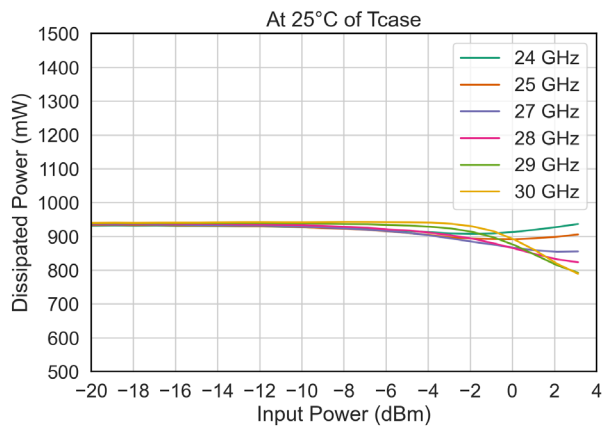
Power Added Efficiency vs. Input Power & Frequency



Drain Current vs. Input Power & Frequency



Dissipated Power vs. Input Power & Frequency

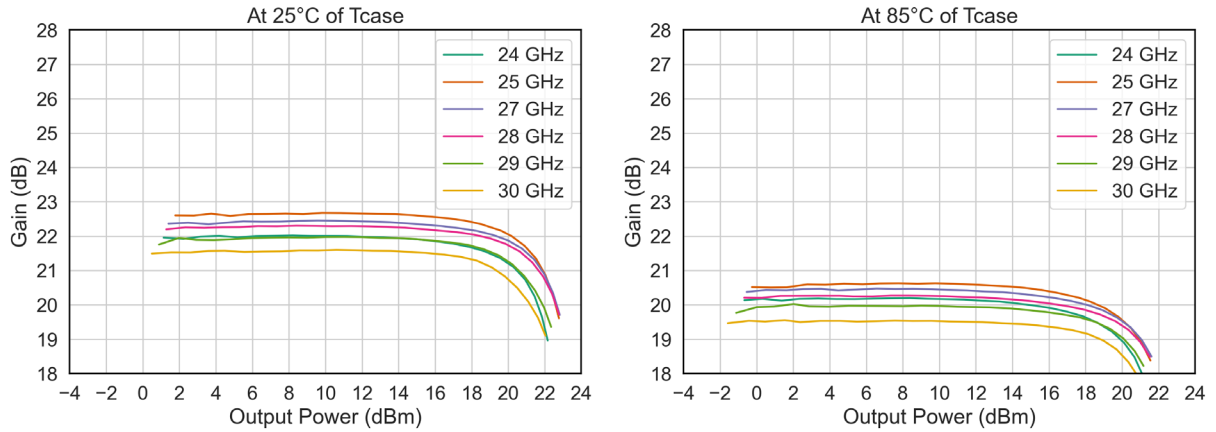


Typical CW Board Measurements vs. Output Power

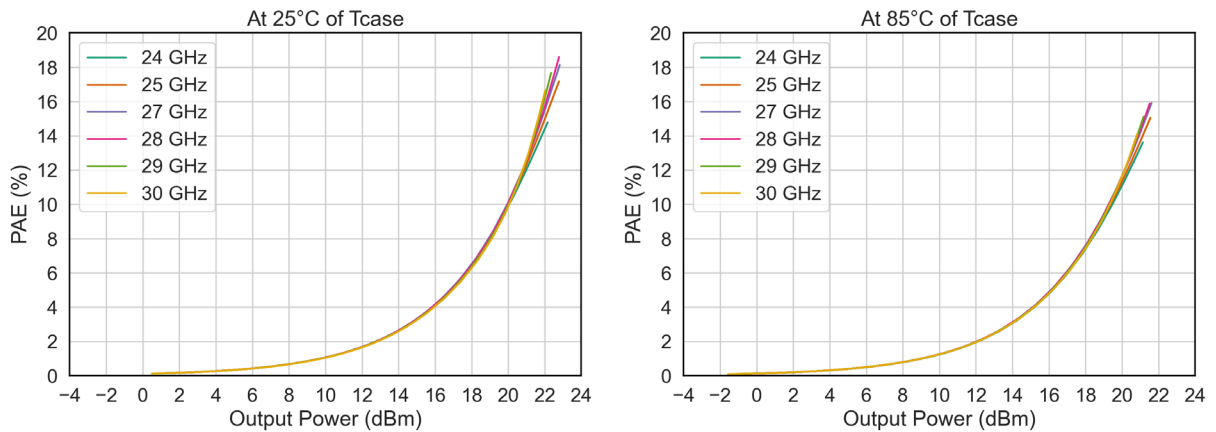
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = +25^\circ C/85^\circ C$

Measurements are given in the QFN access planes

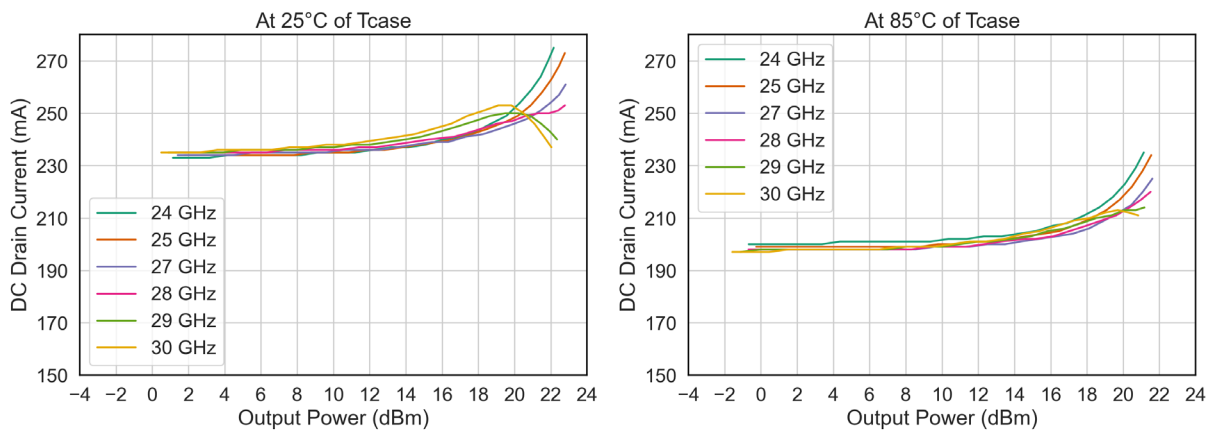
Gain vs. Output Power & Frequency

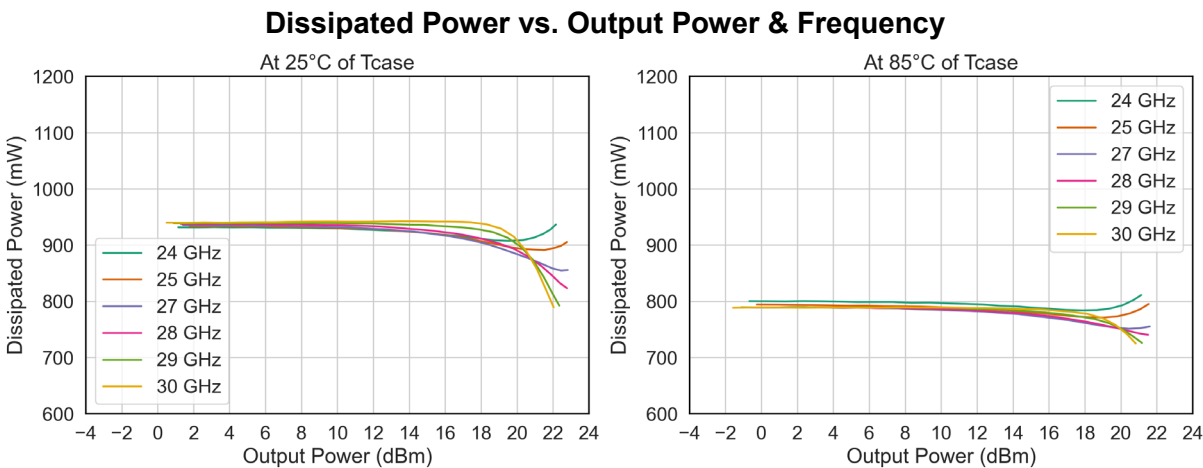


Power Added Efficiency vs. Output Power & Frequency



Drain Current vs. Output Power & Frequency



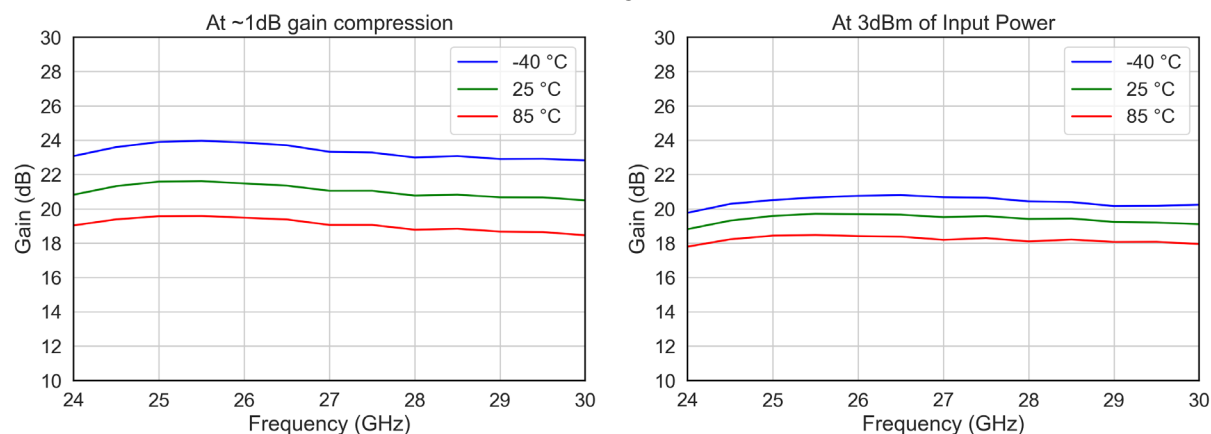


Typical CW Board Measurements vs. Frequency

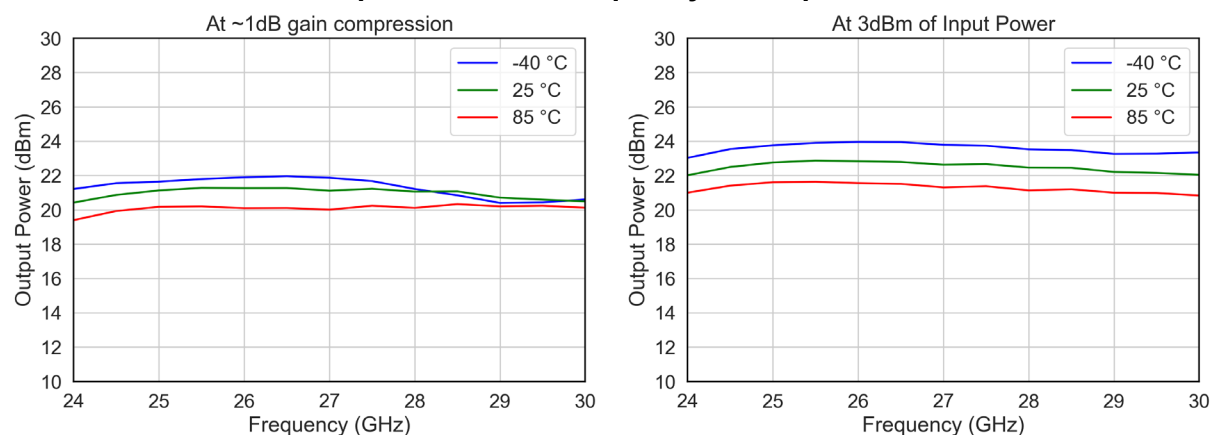
Test conditions : CW, $V_d = +4V$, $I_{dq} = 230mA$, $T_{case} = -40^{\circ}C/25^{\circ}C/85^{\circ}C$

Measurements are given in the QFN access planes

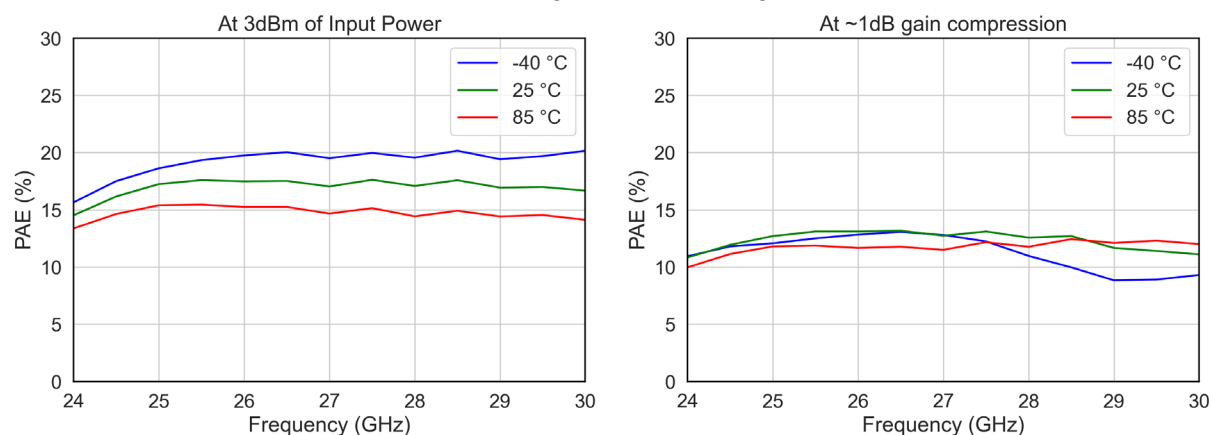
Gain vs. Frequency & Temperature



Output Power vs. Frequency & Temperature

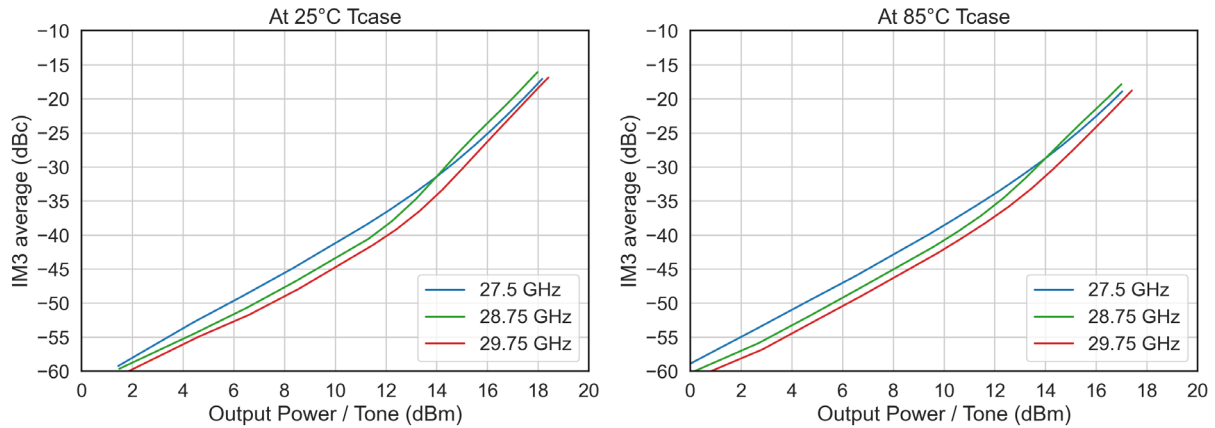


Power Added Efficiency vs. Frequency & Temperature

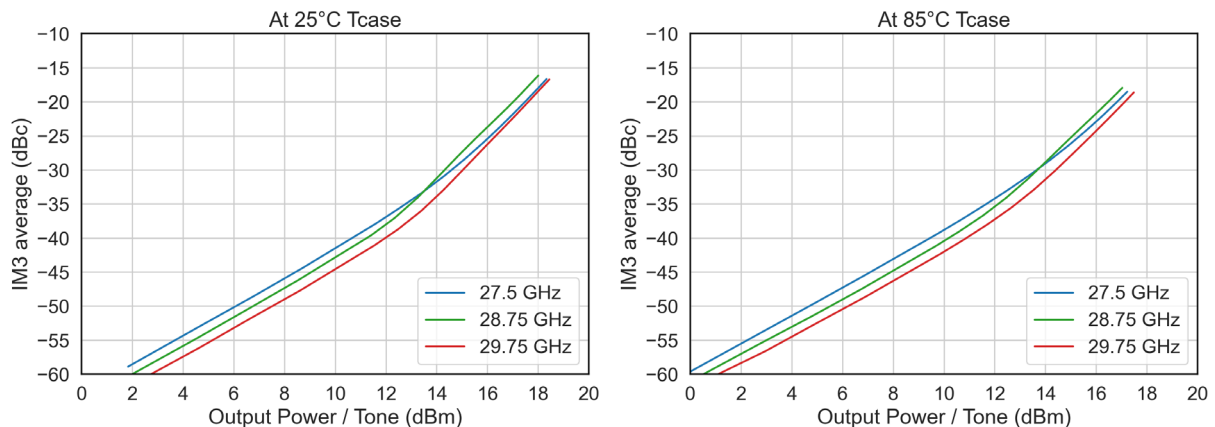


Typical Board Measurements : Modulation Results

Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 10MHz$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Output Power per Tone & Central Frequency

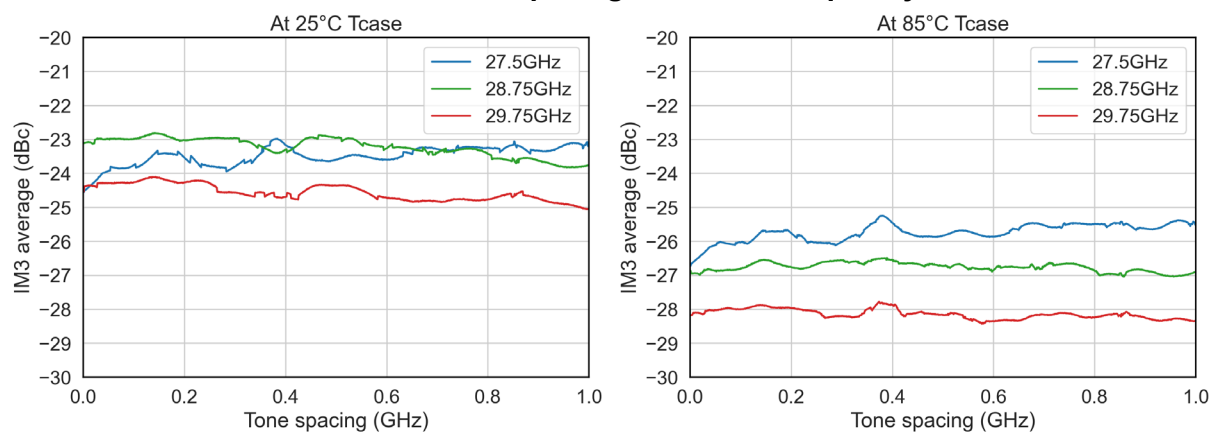
Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 100MHz$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Output Power per Tone & Central Frequency

Typical Board Measurements : Modulation Results

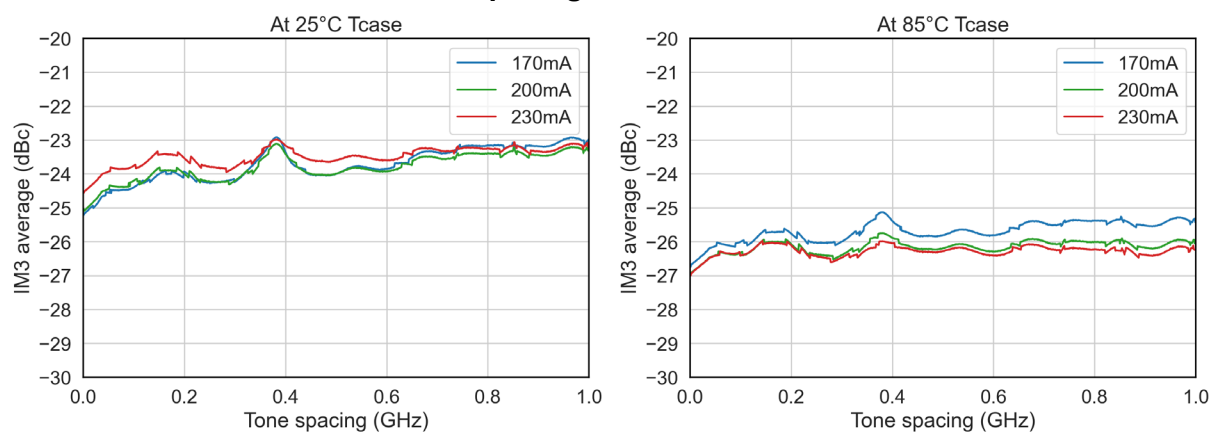
Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $P_{out}/tone = 16dBm$, $T_{case} = +25^{\circ}C/85^{\circ}C$

IMD3 vs. Tone Spacing & Central Frequency



Test conditions : CW dual tones, $V_d = +4V$, $F_c = 27.5GHz$, $P_{out}/tone = 16dBm$, $T_{case} = 25^{\circ}C/85^{\circ}C$

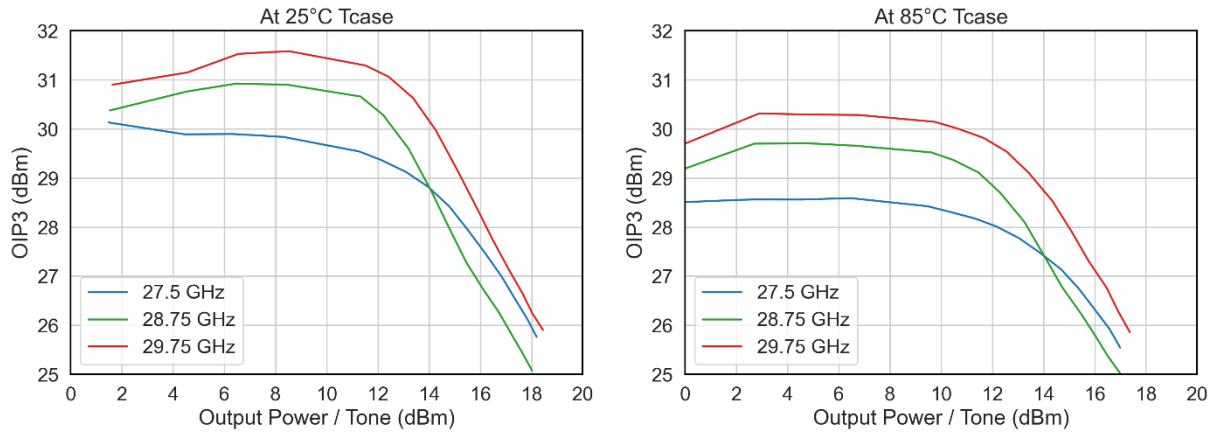
IMD3 vs. Tone Spacing & Quiescent Drain Current



Typical Board Measurements : Modulation Results

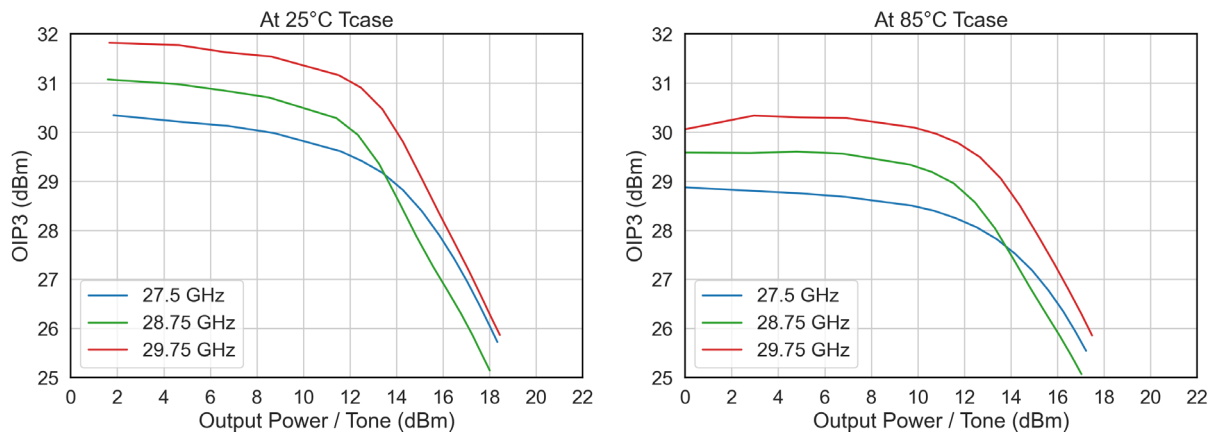
Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 10MHz$, $T_{case} = +25^\circ C/85^\circ C$

OIP3 vs. Output Power per Tone & Central Frequency



Test conditions : CW dual tones, $V_d = +4V$, $I_{dq} = 230mA$, $\Delta f = 100MHz$, $T_{case} = +25^\circ C/85^\circ C$

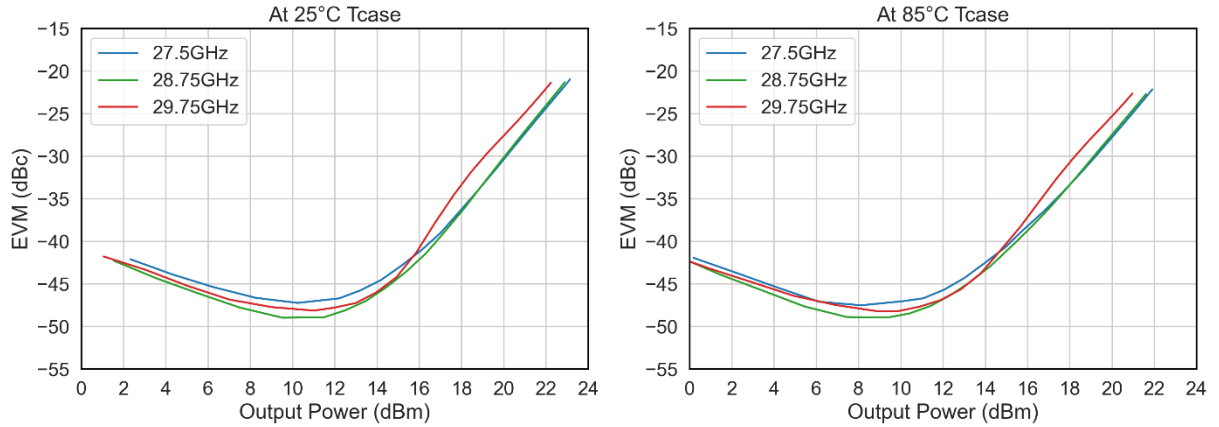
OIP3 vs. Output Power per Tone & Central Frequency



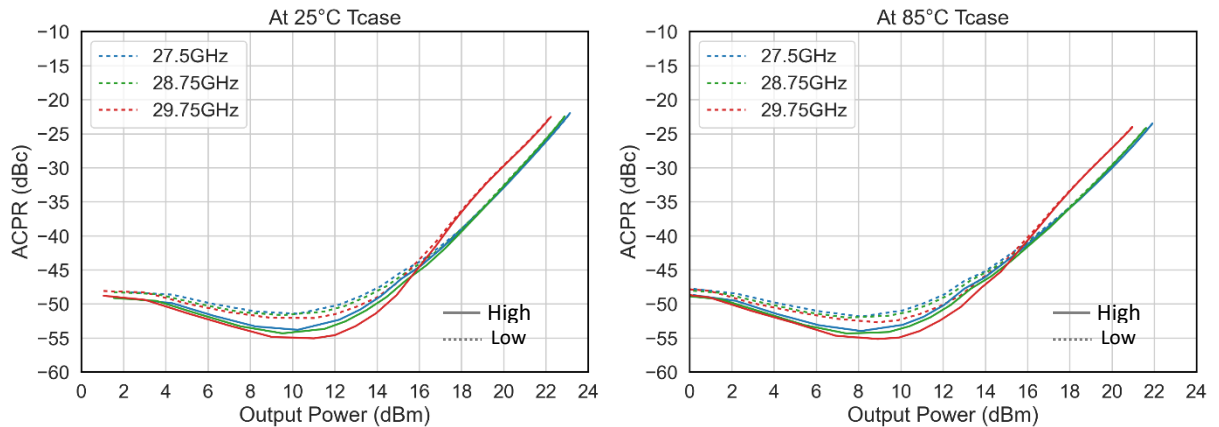
Typical Board Measurements : Modulation Results

Test conditions : $V_d = +4V$, $I_{dq} = 230mA$, 8PSK, BW = 150MHz, Roll-off = 0.2, PAPR = 5.1dB,
 $T_{case} = +25^{\circ}C/85^{\circ}C$

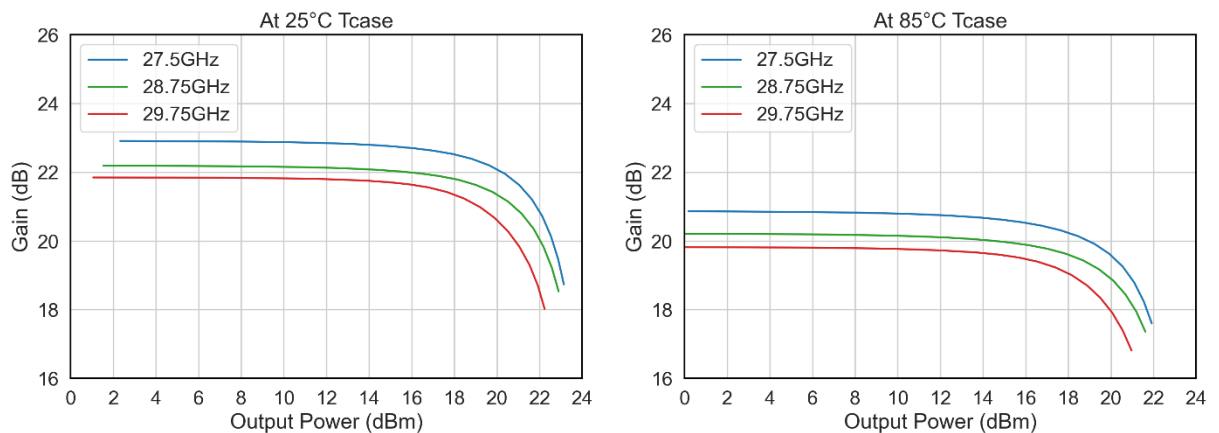
EVM vs. Average Output Power & Central Frequency



ACPR vs. Average Output Power & Central Frequency



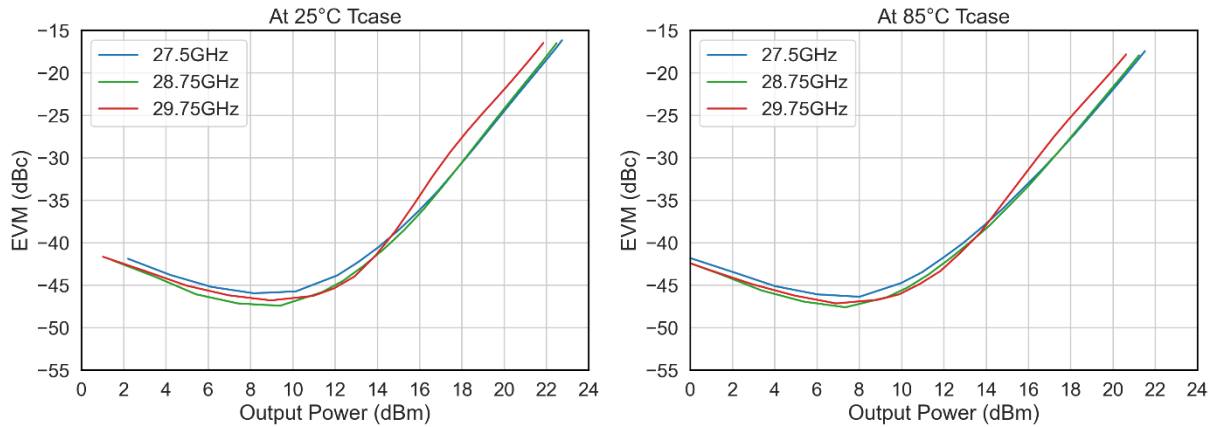
Gain vs. Average Output Power & Central Frequency



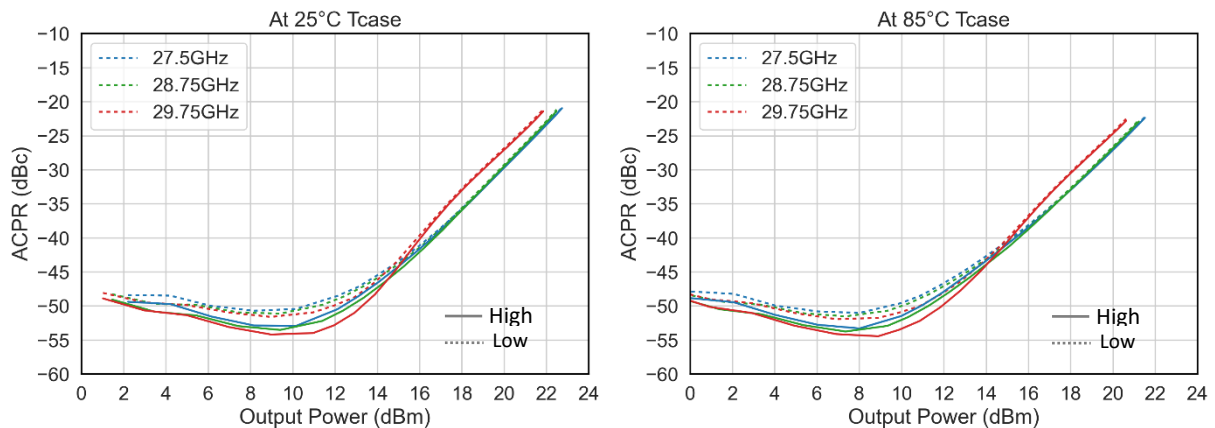
Typical Board Measurements : Modulation Results

Test conditions : $V_d = +4V$, $I_{dq} = 230mA$, 16QAM, BW = 150MHz, Roll-off = 0.2, PAPR = 6.5dB, $T_{case} = +25^{\circ}C/85^{\circ}C$

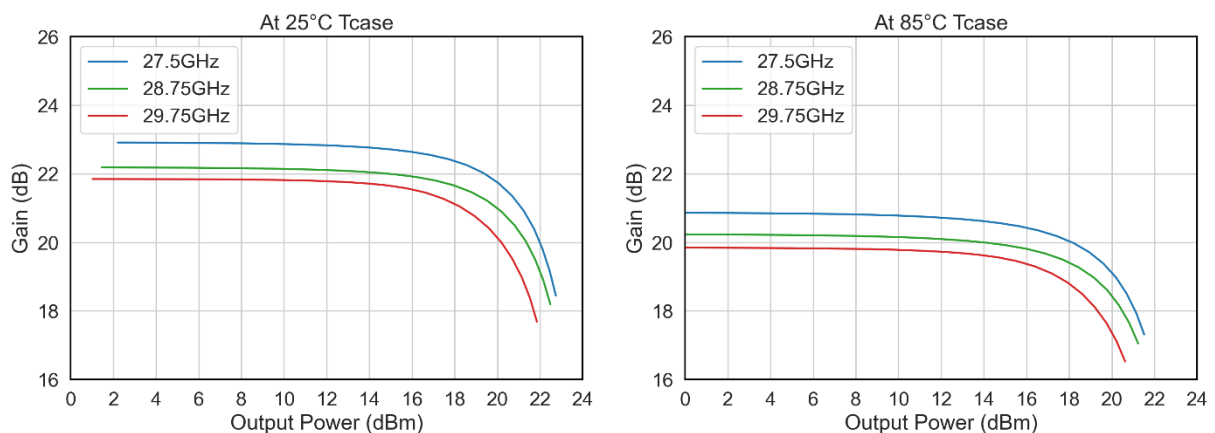
EVM vs. Average Output Power & Central Frequency



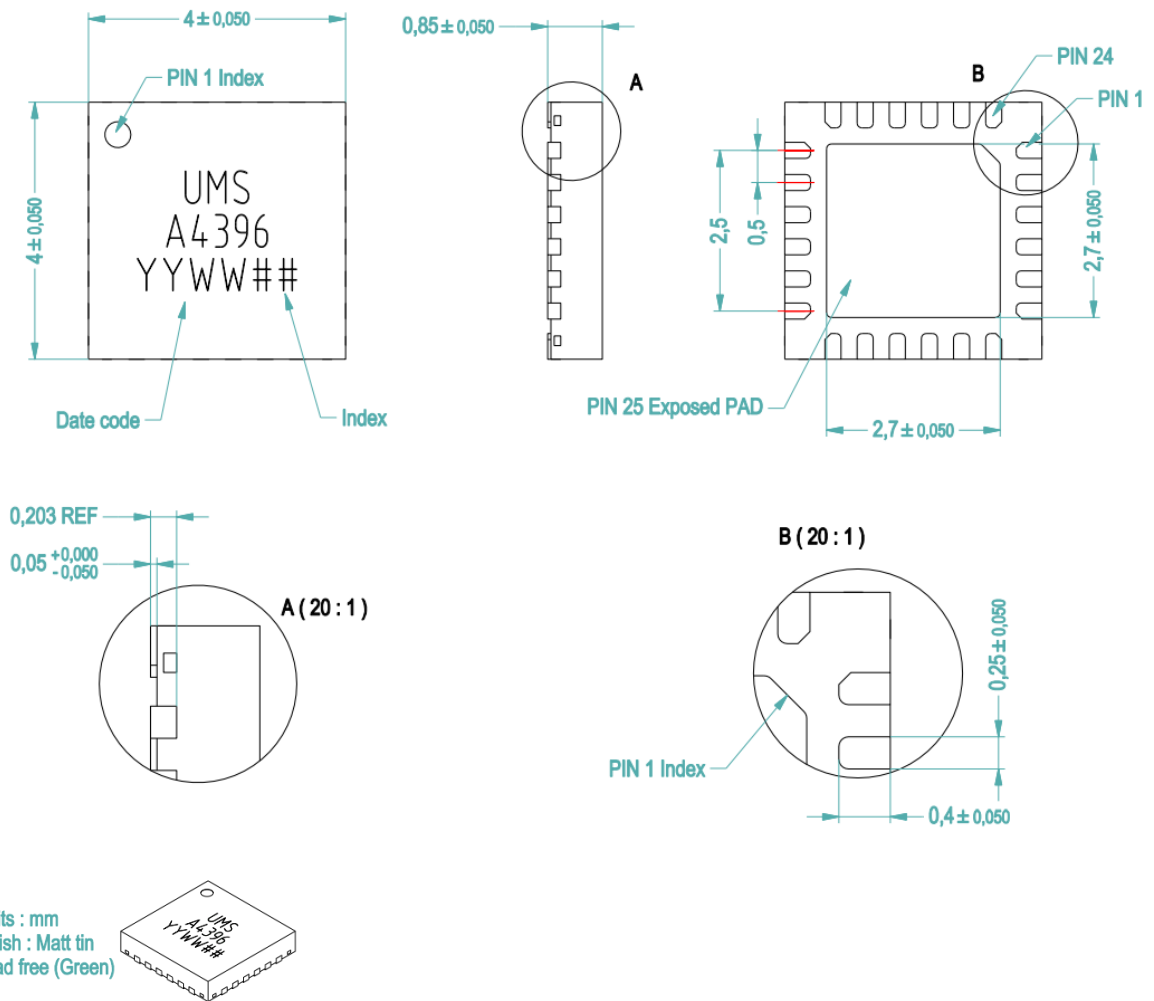
ACPR vs. Average Output Power & Central Frequency



Gain vs. Average Output Power & Central Frequency



Package outline

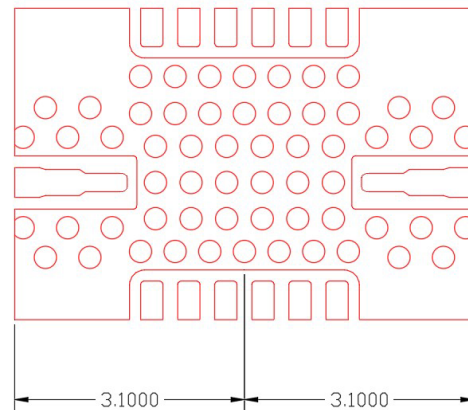


Finish:	Matt Tin Lead Free (Green)	1- NC	11- GND ⁽¹⁾	21- VD3
Units :	mm	2- GND ⁽¹⁾	12- NC	22- VD2
From the standard :	JEDEC MO-220	3- GND ⁽¹⁾	13- GND ⁽¹⁾	23- VD1
	(VGGD)	4- RF in	14- GND ⁽¹⁾	24- NC
NC :	Not Connected	5- GND ⁽¹⁾	15- RF out	25- GND ⁽¹⁾
		6- GND ⁽¹⁾	16- GND ⁽¹⁾	
		7- NC	17- GND ⁽¹⁾	
		8- VG1	18- NC	
		9- VG2	19- NC	
		10- VG3	20- GND ⁽¹⁾	

⁽¹⁾ It is strongly recommended to ground all pins marked “GND” through the PCB. Ensure that the PCB board is designed to provide the best ground to the package.

Definition of measurement reference planes

The reference planes used for measurements given above are symmetrical from the symmetrical axis of the package (see drawing beside). The input and output reference planes are located at 3.1mm offset (input wise and output wise respectively) from this axis.



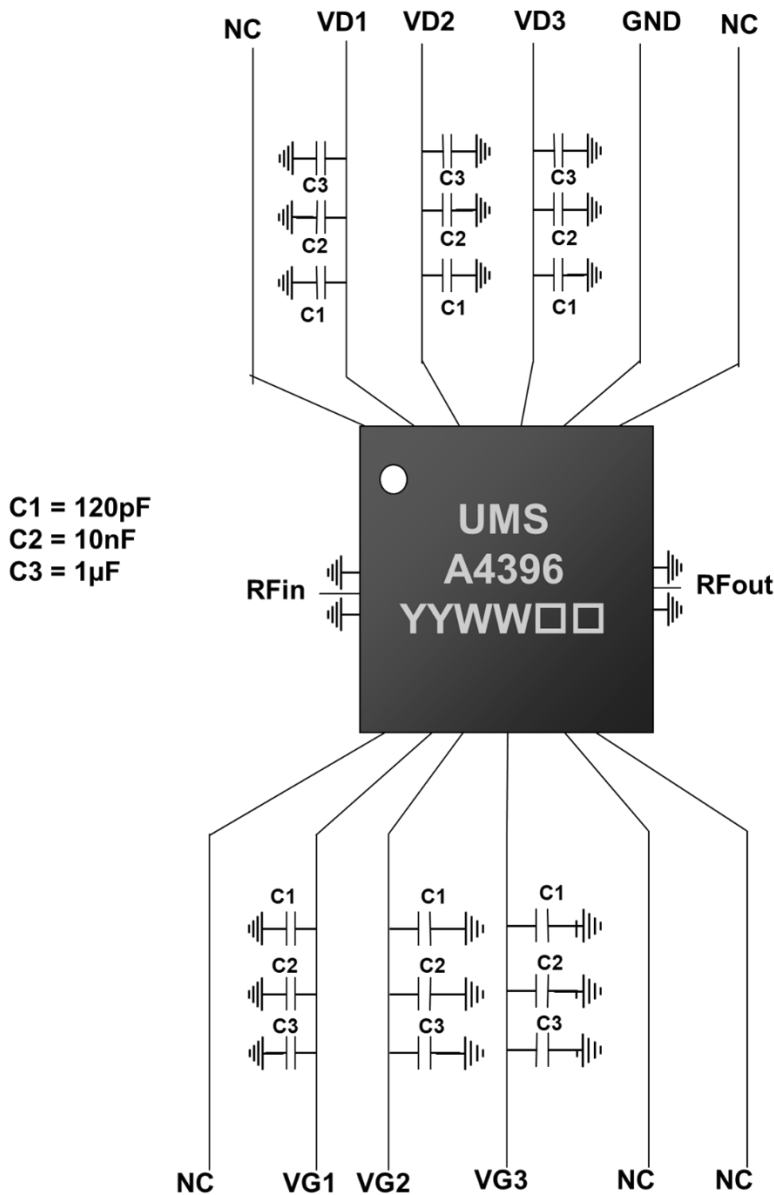
ESD sensitivity

Parameter	Classification	Standard
Human Body Model (HBM)	1A	ANSI/ESDA/JEDEC - JS-001

Package Information

Parameter	Value
Package body material	RoHS-compliant
	Low stress Injection Molded Plastic
Lead finish	100% Matt Tin
Moisture Sensitivity Level	MSL1

Recommended assembly plan

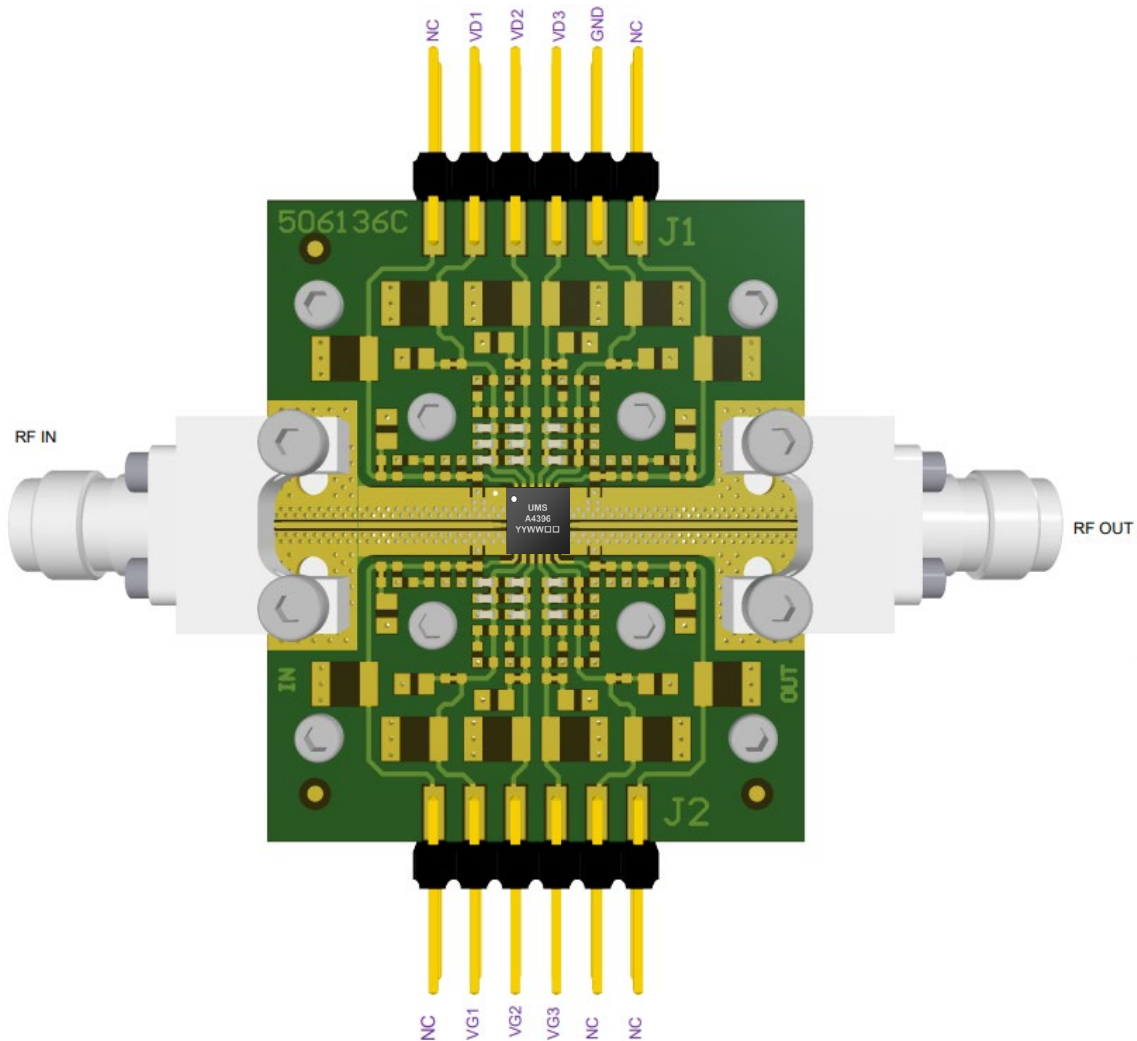


Recommended circuit bonding table

Label	Pin	Type	Decoupling	Comment
VD1, VD2, VD3	21, 22, 23	Vd	120pF, 10nF & 1µF	Drain Supply
VG1, VG2, VG3	8, 9, 10	Vg	120pF, 10nF & 1µF	Gate Supply

Evaluation board

- Compatible with the proposed footprint.
- Based on typically Ro4350B / 8mils or equivalent.
- Using a micro-strip to coplanar transition to access the package.
- Recommended for the implementation of this product on a module board.
- Decoupling capacitors of $120\text{pF} \pm 10\%$, $10\text{nF} \pm 10\%$ & $1\mu\text{F} \pm 10\%$ are recommended for all DC access.
- To ensure safe operation, all measurements must be performed using **shielded cables**, even for DC bias.



Notes

Due to ESD protection circuits on RF input and output, an external capacitance might be requested to isolate the product from external voltage that could be present on the RF accesses.

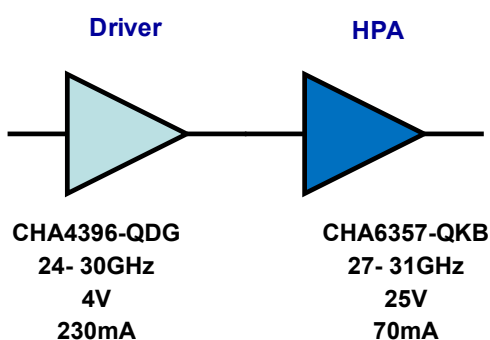
ESD protections are also implemented on gate and control access.

The DC connections do not include any decoupling capacitors in the package. Therefore it is mandatory to provide a good external DC decoupling (120pF, 10nF & 1μF) on the PC board as close as possible to the package.

Recommended UMS Power chain

The CHA4396-QDG is recommended with the CHA6357-QDG.

For more information about the CHA6357-QKB, see our web site <https://www.ums-rf.com>



Recommended package footprint

Refer to the application note AN0017 available at <https://www.ums-rf.com/> for package footprint recommendations.

SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017 available at <https://www.ums-rf.com/>.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com/>.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com/> for ESD sensitivity and handling recommendations for the UMS package products.

Description of Evaluation Board

Refer to the application note AN0031 available at <https://www.ums-rf.com/> for the description of Evaluation Board for Packaged Die and recommendations for this UMS package product.

Ordering request reference

Package: CHA4396-QDG/XY
Stick: XY = 20

Tape & reel: XY = 21

Information furnished is believed to be accurate and reliable. However **United Monolithic Semiconductors S.A.S.** assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of **United Monolithic Semiconductors S.A.S.**. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. **United Monolithic Semiconductors S.A.S.** products are not authorised for use as critical components in life support devices or systems without express written approval from **United Monolithic Semiconductors S.A.S.**